L Number	Hits	Search Text	DB	Time stamp
-	7	(substrate same (insulating or insulator or dielectric) same lectrode same (black near	USPAT; US-PGPUB;	2003/01/26 12:40
		(matrix r matrices)) same transparent same protrusi n)	EPO; JP ; DERWENT; IBM_TDB	:
-	8	(substrate same (insulating or insulator or	USPAT;	2003/01/26
		dielectric) same (black near (matrix or	US-PGPUB;	12:41
		matrices)) same transparent same	EPO; JPO;	
		protrusion)	DERWENT; IBM_TDB	
•	3	(substrate same (insulating or insulator or	USPAT;	2003/01/26
		dielectric) same (black near (matrix or	US-PGPUB;	12:42
		matrices)) same transparent same	EPO; JPO;	
		protrusion) and organic	DERWENT;	
	0500		IBM_TDB	
•	8522	(black near (matrix or matrices))	USPAT;	2003/01/26
			US-PGPUB;	12:42
			EPO; JPO;	
			DERWENT;	
	4513	((black near (matrix or matrices))) and	IBM_TDB	2002/04/06
	4010	transparent	USPAT; US-PGPUB;	2003/01/26 12:42
			EPO; JPO;	12:42
			DERWENT;	
			IBM_TDB	
	2902	(((black near (matrix or matrices))) and	USPAT;	2003/01/26
		transparent) and pixel	US-PGPUB;	12:42
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
'	2729	((((black near (matrix or matrices))) and	USPAT;	2003/01/26
		transparent) and pixel) and substrate	US-PGPUB;	12:43
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	1228	(((((black near (matrix or matrices))) and	USPAT;	2003/01/26
		transparent) and pixel) and substrate) and	US-PGPUB;	12:43
		organic	EPO; JPO;	
			DERWENT;	
	114	/////hlack near/metrix as matrice at the	IBM_TDB	
	114	((((((black near (matrix or matrices)))) and	USPAT;	2003/01/26
		transparent) and pixel) and substrate) and organic) and protrusion	US-PGPUB;	12:43
		יישיייטן מווע פויטנועסוטוו	EPO; JPO;	
			DERWENT; IBM_TDB	
ļ	111	(((((((black near (matrix or matrices))) and	USPAT;	2003/01/26
		transpar nt) and pix I) and substrate) and	US-PGPUB;	2003/01/26 12:43
	İ	rganic) and pr trusi n) and c l r	EPO; JPO;	12143
		Composition of the state of the	DERWENT;	
			IBM_TDB	

•	106	((((((((black n ar (matrix or matrices))) and	USPAT;	2003/01/26
		transparent) and pixel) and substrate) and	US-PGPUB;	12:44
		rganic) and protrusi n) and c l r) and	EPO; JPO;	
		lectr d	DERWENT;	
			IBM_TDB	
-	28	((((((((black n ar (matrix r matric s))) and	USPAT;	2003/01/26
		transparent) and pixel) and substrate) and	US-PGPUB;	12:44
		organic) and protrusion) and color) and	EPO; JPO;	
		electrode) and (black near (matrix or	DERWENT;	
		matrices)).ti,ab,clm.	IBM TDB	

L Number	Hits	Search T xt	DB	Tim stamp
	2731	(transpar nt n ar electrod) n ar10	USPAT;	2003/01/27
		(insulating rinsulat r r dielectric) near10	US-PGPUB;	09:35
		substrat	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric) near10	US-PGPUB;	09:37
		substrate) and ((black near (matrix or	EPO; JPO;	
		matrices)) near5 (transparent near	DERWENT;	
		electrode) near5 protrusion)	IBM_TDB	
	4	((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric) near10	US-PGPUB;	09:40
		substrate) and ((black near (matrix or	EPO; JPO;	
		matrices)) near10 (transparent near	DERWENT;	
		electrode) near10 protrusion)	IBM TDB	
,	4	((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric) near10	US-PGPUB;	09:41
		substrate) and ((black near (matrix or	EPO; JPO;	33.41
		matrices)) near20 (transparent near	DERWENT;	
		electrode) near20 protrusion)	IBM TDB	
	3	((transparent near electrode) near10	USPAT;	2003/01/27
	_	(insulating or insulator or dielectric) near10	US-PGPUB;	09:42
		substrate) and ((black near (matrix or	EPO; JPO;	03.42
		matrices)) same (transparent near	DERWENT;	
		electrode) same protrusion).ti,ab,clm.	IBM TDB	
	3	((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric) near10	US-PGPUB;	09:42
		substrate) and ((black near (matrix or	EPO; JPO;	09.42
		matrices)) same (transparent near2	DERWENT;	
		electrode) same protrusion).ti,ab,clm.	IBM_TDB	
	3	((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric) near10	US-PGPUB;	09:43
		substrate) and ((black near (matrix or	1	09:43
		matrices)) same (transparent near3	EPO; JPO;	
		• •	DERWENT;	
	4	electrode) same protrusion).ti,ab,clm.	IBM_TDB	0000/04/07
	~	((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric) near10	US-PGPUB;	09:43
		substrate) and ((black near (matrix or	EPO; JPO;	
		matrices)) same (transparent near3	DERWENT;	
	40	electrode) same protrusion)	IBM_TDB	
	10	((black near (matrix or matrices)) same	USPAT;	2003/01/27
		(transparent near3 electrode) same	US-PGPUB;	09:45
		protrusion)	EPO; JPO;	
			DERWENT;	
	_	//D. 1	IBM_TDB	,
	1	(((black near (matrix r matric s)) sam	USPAT;	2003/01/27
		(transpar nt n ar3 ctr d) sam	US-PGPUB;	09:45
		pr trusi n)) and organic	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	6	(((black n ar (matrix r matric s)) sam (transpar nt near3 l ctr d) sam protrusion)) and pix l	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/27 09:45	
			IBM TDB		

	420	(US-6504592-\$ r US-6476890-\$ r	USPAT;	2003/01/27
-	130	US-6476898-\$ r US-6437847-\$ or	US-PGPUB;	
		US-6441873-\$ r US-6476882-\$ or	JPO;	00.01
		1	DERWENT	
		US-6392728-\$ r US-6323594-\$ r	DERWENT	
		US-6266121-\$ r US-6215243-\$ or		
		US-6239856-\$ or US-6208394-\$ r		
		US-6175395-\$ or US-6163358-\$ or		
		US-6091472-\$ or US-6069674-\$ or		
		US-6008877-\$ or US-5995190-\$ or		
		US-5999236-\$ or US-5946062-\$ or		
		US-5754267-\$ or US-5805249-\$ or		
		US-5815224-\$ or US-5729317-\$ or		
		US-5742371-\$ or US-5640216-\$).did. or		
		(US-5654781-\$ or US-5477351-\$ or		
		US-6433852-\$ or US-6504591-\$ or		
		US-6351078-\$ or US-6498592-\$ or		
		US-6239470-\$ or US-6262784-\$ or		
	ļ	US-6243146-\$ or US-6114715-\$ or		
		US-6198520-\$ or US-6162510-\$ or		
		US-6040887-\$ or US-6057896-\$ or		
		US-5870160-\$ or US-5943107-\$ or		
		US-6034747-\$ or US-5478611-\$ or		
		US-5815226-\$ or US-5739880-\$ or		
		US-5721076-\$ or US-6424402-\$ or		
		US-6169293-\$ or US-6275280-\$ or		
	Ì	US-5982471-\$ or US-6066448-\$ or		
		US-5952708-\$).did. or (US-5843332-\$ or		
		US-5558927-\$ or US-5619097-\$ or		
		US-6266117-\$ or US-6300152-\$ or		
		US-6509939-\$ or US-6429916-\$ or		
		US-6429917-\$ or US-6476783-\$ or		
		US-6411360-\$ or US-6296750-\$ or		
		US-6373540-\$ or US-6392729-\$ or		
		US-6407782-\$ or US-6356330-\$ or		
		US-6281957-\$ or US-6221543-\$ or		
		US-6224730-\$ or US-6208404-\$ or		
		US-6162654-\$ or US-6157426-\$ or		
		US-6068750-\$ or US-6117294-\$ or		
		US-6118506-\$ or US-6122025-\$ or		
		US-6005651-\$ or US-5956109-\$).did. or		
		(US-5754263-\$ or US-5781254-\$ or		
		US-5689318-\$ or US-5691788-\$ or		
		US-5703668-\$ or US-5633739-\$ or		
		US-5631753-\$ or US-5299041-\$ or		
		US-5495354-\$ or US-5619357-\$ or		
		US-5626796-\$ or US-6388722-\$ or		
		US-6404480-\$ or US-6429059-\$ or		
		US-6433842-\$ r US-6489720-\$ or		
		US-6013930-\$ r US-6121660-\$ r		
		US-6124604-\$ r US-6177974-\$ r		
		US-6204535-\$ or US-6219113-\$ r		
		US-6281952-\$ r US-5529524-\$ or		
		US-5548181-\$ or US-5587623-\$ r		
		US-5847792-\$).did. or (US-6327016-\$).did. or		
S arch His	t ry 2/9/0	3 7,158:20010049656-\$ or US-20010013913-\$ or		
C:\APPS\ a	st\workspa	ce 1.6930320056958-\$)spid. r		
	•	(JP-2001013312-\$ r JP-2001059968-\$ r		

	1	((US-6504592-\$ r US-6476890-\$ r	USPAT;	2003/01/27
	•	US-6476898-\$ r US-6437847-\$ r	US-PGPUB;	09:56
		US-6441873-\$ or US-6476882-\$ r	EPO; JP ;	
		US-6392728-\$ or US-6323594-\$ or	DERWENT;	
		US-6266121-\$ or US-6215243-\$ r	IBM TDB	
		US-6239856-\$ or US-6208394-\$ r	15155	
		US-6175395-\$ or US-6163358-\$ or		
		US-6091472-\$ or US-6069674-\$ or		
		US-6008877-\$ or US-5995190-\$ or		
		US-5999236-\$ or US-5946062-\$ or		
		US-5754267-\$ or US-5805249-\$ or		
		US-5815224-\$ or US-5729317-\$ or		
		US-5742371-\$ or US-5640216-\$).did. or		
		(US-5654781-\$ or US-5477351-\$ or		
		US-6433852-\$ or US-6504591-\$ or		
		US-6351078-\$ or US-6498592-\$ or		
		US-6239470-\$ or US-6262784-\$ or		
		US-6243146-\$ or US-6114715-\$ or		
		US-6198520-\$ or US-6162510-\$ or		
		US-6040887-\$ or US-6057896-\$ or		
		US-5870160-\$ or US-5943107-\$ or		
		US-6034747-\$ or US-5478611-\$ or		
		US-5815226-\$ or US-5739880-\$ or		
1		US-5721076-\$ or US-6424402-\$ or		
		US-6169293-\$ or US-6275280-\$ or		
		US-5982471-\$ or US-6066448-\$ or		
		US-5952708-\$).did. or (US-5843332-\$ or		
		US-5558927-\$ or US-5619097-\$ or		
		US-6266117-\$ or US-6300152-\$ or		
		US-6509939-\$ or US-6429916-\$ or		
		US-6429917-\$ or US-6476783-\$ or		
		US-6411360-\$ or US-6296750-\$ or		
		US-6373540-\$ or US-6392729-\$ or		
		US-6407782-\$ or US-6356330-\$ or		
		US-6281957-\$ or US-6221543-\$ or		
		US-6224730-\$ or US-6208404-\$ or		
		US-6162654-\$ or US-6157426-\$ or		
		US-6068750-\$ or US-6117294-\$ or		
		US-6118506-\$ or US-6122025-\$ or		
		US-6005651-\$ or US-5956109-\$).did. or		
		(US-5754263-\$ or US-5781254-\$ or		
		US-5689318-\$ or US-5691788-\$ or		
		US-5703668-\$ or US-5633739-\$ or		
		US-5631753-\$ or US-5299041-\$ or		
		US-5495354-\$ or US-5619357-\$ or		
		US-5626796-\$ or US-6388722-\$ or		
		US-6404480-\$ or US-6429059-\$ or		
		US-6433842-\$ or US-6489720-\$ or		
		US-6013930-\$ r US-6121660-\$ r		
į		US-6124604-\$ r US-6177974-\$ r		
		US-6204535-\$ r US-6219113-\$ or		
		US-6281952-\$ r US-5529524-\$ or		
1				
		US-5548181-\$ r US-5587623-\$ r		
		US-5847792-\$).did. r (US-6327016-\$).did. u		
		3 ДЫЗ-2014(1049656-3 r US-20010013913-\$ r ce ы8939320050958-\$)spid. r		
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	1	(((insulating rinsulator or diel ctric) sam	USPAT;	2003/01/27
		substrat) and (transparent n ar electr d)	US-P PUB;	09:56
		and (bla k near (matrix or matrices)) and	EPO; JPO;	
		pr trusion and (col r near filter) and rganic	DERWENT;	
		and (photosensitive) and (lith grahpy r	IBM_TDB	
		ph tolith graphy) and pix l).ti,ab,clm.		
•	1	(((insulating or insulator or dielectric) same	USPAT;	2003/01/27
		substrate) and (transparent near electrode)	US-PGPUB;	09:57
		and (black near (matrix or matrices)) and	EPO; JPO;	
		protrusion and (color near filter) and organic	DERWENT;	
		and (photosensitive) and pixel).ti,ab,clm.	IBM_TDB	
-	1	(((insulating or insulator or dielectric) same	USPAT;	2003/01/27
		substrate) and (transparent near electrode)	US-PGPUB;	09:57
		and (black near (matrix or matrices)) and	EPO; JPO;	
		protrusion and (color near filter) and organic	DERWENT;	
		and pixel).ti,ab,clm.	IBM_TDB	
	36	(((insulating or insulator or dielectric) same	USPAT;	2003/01/27
		substrate) and (transparent near electrode)	US-PGPUB;	09:58
		and (black near (matrix or matrices)) and	EPO; JPO;	
		protrusion and (color near filter) and organic	DERWENT;	
		and pixel)	IBM TDB	
_	28096	((((insulating or insulator or dielectric) same	USPAT:	2003/01/27
	20030	substrate) and (transparent near electrode)	US-PGPUB;	10:00
	:	and (black near (matrix or matrices)) and	EPO; JPO;	
		protrusion and (color near filter) and organic	DERWENT;	
		and pixel)) amd (black near (matrix or	IBM_TDB	
		matrices)).ti,ab,clm.		
_	10	((((insulating or insulator or dielectric) same	USPAT;	2003/01/27
- -	10	substrate) and (transparent near electrode)	US-PGPUB;	10:00
		and (black near (matrix or matrices)) and	EPO; JPO;	10.00
		protrusion and (color near filter) and organic	DERWENT;	
		,	IBM_TDB	
		and pixel)) and (black near (matrix or matrices)).ti,ab,clm.	IBM_IDB	
		1	USPAT;	2003/01/27
•	9	(((((insulating or insulator or dielectric)	1	
		same substrate) and (transparent near	US-PGPUB;	10:01
		electrode) and (black near (matrix or	EPO; JPO;	
		matrices)) and protrusion and (color near	DERWENT;	
		filter) and organic and pixel)) and (black	IBM_TDB	
		near (matrix or matrices)).ti,ab,clm.) and		
	_	substrate.ti,ab,clm.	ucp.a.T	2002/04/27
-	8	((((((insulating or insulator or dielectric)	USPAT;	2003/01/27
		same substrate) and (transparent near	US-PGPUB;	10:01
		electrode) and (black near (matrix or	EPO; JPO;	
		matrices)) and protrusion and (color near	DERWENT;	
		filter) and organic and pixel)) and (black	IBM_TDB	
		near (matrix or matrices)).ti,ab,clm.) and		
		substrate.ti,ab,clm.) and		
		transpar nt.ti,ab,clm.		İ

•	5	(((((((insulating rinsulator rdiel ctri)	USPAT;	2003/01/27
		sam substrat) and (transparent near	US-PGPUB;	10:02
		lectrod) and (black near (matrix r	EPO; JPO;	
		matrices)) and protrusion and (col r n ar	DERWENT;	
		filter) and rganic and pixel)) and (black	IBM_TDB	
		near (matrix or matric s)).ti,ab,clm.) and		
		substrate.ti,ab,clm.) and		
		transparent.ti,ab,clm.) and data		
-	4	(((((((insulating or insulator or dielectric)	USPAT;	2003/01/27
		same substrate) and (transparent near	US-PGPUB;	11:12
		electrode) and (black near (matrix or	EPO; JPO;	
		matrices)) and protrusion and (color near	DERWENT;	
		filter) and organic and pixel)) and (black	IBM_TDB	
		near (matrix or matrices)).ti,ab,clm.) and		
		substrate.ti,ab,clm.) and		
		transparent.ti,ab,clm.) and data) and gate		
-	1	(black near matrix) and chrome and (color	USPAT;	2003/01/27
		near filter) and (gate near line) and (data	US-PGPUB;	11:14
		near line) and (pixel near electrode) and	EPO; JPO;	
		(redundant near data)	DERWENT;	
			IBM_TDB	
 -	3	(black near matrix) and (color near filter)	USPAT;	2003/01/27
		and (gate near line) and (data near line) and	US-PGPUB;	11:18
		(pixel near electrode) and (redundant near	EPO; JPO;	
		data)	DERWENT;	
		•	IBM_TDB	
_	3559	(transparent near2 electrode near3	USPAT;	2003/01/27
		(insulating or insulator or dielectric))	US-PGPUB;	11:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	17	((transparent near2 electrode near3	USPAT;	2003/01/27
		(insulating or insulator or dielectric))) and	US-PGPUB;	11:23
		((light near (block or blocking or blocked))	EPO; JPO;	
		near5 metal)	DERWENT;	
		,	IBM_TDB	
_	7	(((transparent near2 electrode near3	USPAT;	2003/01/27
		(insulating or insulator or dielectric))) and	US-PGPUB;	11:24
		((light near (block or blocking or blocked))	EPO; JPO;	
		near5 metal)) and ((light near (block or	DERWENT;	
		blocking or blocked)) near5 metal near10	IBM_TDB	
		transparent)		
_	1	((((transparent near2 electrode near3	USPAT;	2003/01/27
-	•	(insulating or insulator or dielectric))) and	US-PGPUB;	11:24
		((light near (block or blocking or blocked))	EPO; JPO;	
		near5 metal)) and ((light near (block or	DERWENT;	
		blocking or blocked)) near5 metal near10	IBM_TDB	
		transpar nt)) and (protrusi n\$10 near5		
		organic)		
L	<u></u>	viganic)	1	

PUB; 11:25 PO; ENT; DB 2003/01/27 11:25 PO; ENT; DB 2003/01/27 11:26
PO; ENT; DB 2003/01/27 11:25 PO; ENT; DB 2003/01/27 PUB; 11:26
; 2003/01/27 PUB; 11:25 PO; ENT; DB 2003/01/27 PUB; 11:26
; 2003/01/27 PUB; 11:25 PO; ENT; DB 2003/01/27 PUB; 11:26
; 2003/01/27 PUB; 11:25 PO; ENT; DB 2003/01/27 PUB; 11:26
PUB; 11:25 PO; ENT; DB 2003/01/27 PUB; 11:26
PUB; 11:25 PO; ENT; DB 2003/01/27 PUB; 11:26
PUB; 11:25 PO; ENT; DB 2003/01/27 PUB; 11:26
PO; ENT; DB 2; 2003/01/27 PUB; 11:26
ENT; DB 2003/01/27 PUB; 11:26
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PUB; 11:26
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r; 2003/01/27
PUB; 11:28
PO;
ENT;
DB

•	2	((((((((transparent near2 electr d n ar3	USPAT;	2003/01/27
		(insulating or insulator or diel ctric))) and ((light near (bl ck or bl cking r blo k d)) n ar5 metal)) and ((light n ar (block or blocking r blocked)) n ar5 metal near10 transpar nt)) and (protrusi n\$10 and organic)) and photosensitive) and pixel) and	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	11:28
		(black near (matrix or matrices))) and (transparent near electrode)) and (black near (matrix or matrices))		
	2	((((((((((((((((((((((((((((((((((((((USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/27 12:15
,		(black near (matrix or matrices))) and (transparent near electrode)) and (black near (matrix or matrices))) and (mask or lithograp\$7 or photolithograp\$7 or photo-litho\$7)		
	0	((((((((((((((((((((((((((((((((((((((USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/27 12:16
	2	technologies") qbetech or "qbe tech" or "qbe technologies" or "aqcess technologies"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/27 12:44
•	449	((transparent near electrode) near10 (insulating or insulator)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/27 12:44
-	648	((transparent near electrode) near10 (insulating or insulator or di ctric)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/27 12:45

		444	HCDAT.	2002/04/27
-	2	(((transparent n ar electrod) n ar10	USPAT; US-PGPUB;	2003/01/27 12:46
		(insulating or insulator or di ctric)) sam		12:40
		(black n ar (matrix or matrices)) same	EPO; JPO; DERWENT;	
		protrusi n).clm.	•	'
			IBM_TDB	2003/01/27
-	2	((((transparent n ar electrod) near10	USPAT;	
		(insulating or insulator or dielectric)) same	US-PGPUB;	12:47
	!	(black near (matrix or matrices)) same	EPO; JPO;	
		protrusion).clm.) and photosensitive	DERWENT;	
			IBM_TDB	
-	2	(((((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric)) same	US-PGPUB;	12:48
		(black near (matrix or matrices)) same	EPO; JPO;	
		protrusion).clm.) and photosensitive) and	DERWENT;	
		(color near filter)	IBM_TDB	
-	1	(((((transparent near electrode) near10	USPAT;	2003/01/27
		(insulating or insulator or dielectric)) same	US-PGPUB;	12:48
		(black near (matrix or matrices)) same	EPO; JPO;	
		protrusion).clm.) and photosensitive) and	DERWENT;	
		(color near filter)) and (method or	IBM_TDB	
		process).clm.		
_	2	((transparent near electrode) and (black	USPAT;	2003/01/27
		near (matrix or matrices)) and	US-PGPUB;	12:58
		(photosensitive) and (etch or etching or	EPO; JPO;	
		etched) and mask and (method or	DERWENT;	
		process)).clm.	IBM_TDB	
_	6	((transparent near electrode) and (black	USPAT;	2003/01/27
		near (matrix or matrices)) and (etch or	US-PGPUB;	12:52
		etching or etched) and mask and (method or	EPO; JPO;	
		process)).clm.	DERWENT;	
		process//.cim	IBM_TDB	
	_	(//transparent many algetrada) and (black	USPAT;	2003/01/27
•	3	(((transparent near electrode) and (black	US-PGPUB;	12:51
		near (matrix or matrices)) and (etch or	1	12.31
		etching or etched) and mask and (method or	EPO; JPO;	
		process)).clm.) and photosensitive	DERWENT;	
			IBM_TDB	2002/04/27
-	17	((transparent) and (black near (matrix or	USPAT;	2003/01/27
		matrices)) and (etch or etching or etched)	US-PGPUB;	12:52
		and mask and (method or process)).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4	(((transparent) and (black near (matrix or	USPAT;	2003/01/27
		matrices)) and (etch or etching or etched)	US-PGPUB;	12:52
		and mask and (method or process)).clm.)	EPO; JPO;	
		and photosensitive.clm.	DERWENT;	
			IBM_TDB	
•	5	(((transparent) and (black near (matrix or	USPAT;	2003/01/27
		matric s)) and (et h or etching r etched)	US-PGPUB;	12:53
		and mask and (m thod or proc ss)).clm.)	EPO; JPO;	1
		and ph t s nsitiv	DERWENT;	
			IBM_TDB	

•	23486	ph t sensitiv .clm.	USPAT;	2003/01/27
			US-PGPUB;	12:54
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	104	ph tos nsitiv .clm. and (black near (matrix	USPAT;	2003/01/27
		or matrices)).clm.	US-PGPUB;	12:55
		"	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	87	(photosensitive.clm. and (black near (matrix	USPAT;	2003/01/27
	0,	or matrices)).clm.) and (method or	US-PGPUB;	12:55
		process).clm.	EPO; JPO;	12.55
		process).cim.		
			DERWENT;	
	40		IBM_TDB	0000/04/07
•	12	((photosensitive.clm. and (black near	USPAT;	2003/01/27
		(matrix or matrices)).clm.) and (method or	US-PGPUB;	12:56
		process).clm.) and (etch or etching or	EPO; JPO;	
		etched).clm.	DERWENT;	
			IBM_TDB	
-	11	(((photosensitive.clm. and (black near	USPAT;	2003/01/27
		(matrix or matrices)).clm.) and (method or	US-PGPUB;	12:57
		process).clm.) and (etch or etching or	EPO; JPO;	
		etched).clm.) and transparent	DERWENT;	
			IBM_TDB	
-	4	((transparent near electrode) and (black	USPAT;	2003/01/27
		near (matrix or matrices)) and	US-PGPUB;	13:00
		(photosensitive or resin or epoxy) and (etch	EPO; JPO;	
		or etching or etched) and mask and (method	DERWENT;	
		or process)).clm.	IBM_TDB	
_	10	((transparent) and (black near (matrix or	USPAT;	2003/01/27
_		matrices)) and (photosensitive or resin or	US-PGPUB;	13:01
		epoxy) and (etch or etching or etched) and	EPO; JPO;	13.01
		mask and (method or process)).clm.	DERWENT;	
			IBM_TDB	0000/04/07
•	10	(((transparent) and (black near (matrix or	USPAT;	2003/01/27
		matrices)) and (photosensitive or resin or	US-PGPUB;	13:02
		epoxy) and (etch or etching or etched) and	EPO; JPO;	
		mask and (method or process)).clm.) and	DERWENT;	
		(mask or masking or masked)	IBM_TDB	
•	10	(((transparent) and (black near (matrix or	USPAT;	2003/01/27
		matrices)) and (photosensitive or resin or	US-PGPUB;	13:03
		epoxy) and (etch or etching or etched) and	EPO; JPO;	
		mask and (method or process)).clm.) and	DERWENT;	
		(mask or masking or masked).clm.	IBM_TDB	
•	24	((black near (matrix or matrices)) and	USPAT;	2003/01/27
		(transparent same electrode same	US-PGPUB;	13:06
		substrat) and (mask or masking r masked)	EPO; JPO;	
		and (m th d or proc ss)).clm.	DERWENT;	
		and the till doe processjj.chm.	· -	1
	<u> </u>		IBM_TDB	

-	4	(((black near (matrix or matrices)) and	USPAT;	2003/01/27
		(transpar nt same ctrode same	US-PGPUB;	13:07
		substrat) and (mask or masking r masked)	EPO; JPO;	
		and (m th d r process)).clm.) and	DERWENT:	
		(ph to\$15).clm.	IBM TDB	
	18	(((black near (matrix or matrices)) and	USPAT;	2003/01/27
-	18		•	13:11
		(transparent same electrode same	US-PGPUB;	13:11
		substrate) and (mask or masking or masked)	EPO; JPO;	
		and (method or process)).clm.) and	DERWENT;	
		(photosensitive or photoresist or	IBM_TDB	
		photo-sensitive or photo-resist or resin or		
		epoxy or resist).clm.		
-	13	((((black near (matrix or matrices)) and	USPAT;	2003/01/27
		(transparent same electrode same	US-PGPUB;	13:13
		substrate) and (mask or masking or masked)	EPO; JPO;	
		and (method or process)).clm.) and	DERWENT;	
		(photosensitive or photoresist or	IBM_TDB	
		photo-sensitive or photo-resist or resin or		
		epoxy or resist).clm.) and (color near filter)		
_	2	(((((black near (matrix or matrices)) and	USPAT;	2003/01/27
-	~	*****	US-PGPUB;	13:13
		(transparent same electrode same	i -	13.13
		substrate) and (mask or masking or masked)	EPO; JPO;	
		and (method or process)).clm.) and	DERWENT;	
		(photosensitive or photoresist or	IBM_TDB	
		photo-sensitive or photo-resist or resin or		
		epoxy or resist).clm.) and (color near filter))		
		and chrome		
-	8	(((((black near (matrix or matrices)) and	USPAT;	2003/01/27
		(transparent same electrode same	US-PGPUB;	13:20
		substrate) and (mask or masking or masked)	EPO; JPO;	
		and (method or process)).clm.) and	DERWENT;	
		(photosensitive or photoresist or	IBM_TDB	
		photo-sensitive or photo-resist or resin or		
		epoxy or resist).clm.) and (color near filter))		
		and ((black near (matrix or matrices))		
		near10 (resin or epoxy or photosensitive or		
		,		
		photo-sensitive or photoresist or resist or	1	
	_	photo-resist)).clm.	HODAT	2002/04/27
•	2	(substrate and (insulating or insulator or	USPAT;	2003/01/27
		dielectric) and (gate near line) and (data	US-PGPUB;	13:24
		near line) and (pixel same electrode) and	EPO; JPO;	
		redundant and (switch or switching or	DERWENT;	
		switched) and protrusion).ti,ab,clm.	IBM_TDB	
•	2	(substrate and (insulating or insulator or	USPAT;	2003/01/27
		dielectric) and (gate near line) and (data	US-PGPUB;	13:26
		near line) and (pixel same electrode) and	EPO; JPO;	
		(redundant near data) and	DERWENT;	
		protrusi n).ti,ab,clm.	IBM_TDB	
			USPAT;	2003/01/27
•	2	(substrat and (insulating or insulat r or	1	
		diel ctric) and (gat n ar lin) and (data	US-PGPUB;	13:28
		n ar lin) and pix I and (r dundant near	EPO; JPO;	
		data) and pr trusion).ti,ab,clm.	DERWENT;	
			IBM_TDB	

•	2	(substrat and (insulating rinsulat ror	USPAT;	2003/01/27
		diel ctric) and (gat) and (data) and pix l	US-P PUB;	13:30
		and (r dundant near data) and	EPO; JPO;	
		pr trusi n).ti,ab,clm.	DERWENT;	
			IBM_TDB	
-	2	(substrate and (insulating rinsulat r r	USPAT;	2003/01/27
		dielectric) and (gate) and (data) and pixel	US-PGPUB;	13:30
		and (redundant) and protrusion).ti,ab,clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	27	(substrate and (insulating or insulator or	USPAT;	2003/01/27
		dielectric) and (gate) and (data) and pixel	US-PGPUB;	13:32
		and protrusion).ti,ab,clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	,
-	3	((substrate and (insulating or insulator or	USPAT;	2003/01/27
		dielectric) and (gate) and (data) and pixel	US-PGPUB;	13:31
		and protrusion).ti,ab,clm.) and redundant	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	4	(substrate and (insulating or insulator or	USPAT;	2003/01/27
		dielectric) and (gate) and (data) and pixel	US-PGPUB;	13:33
		and protrusion and (redundant or	EPO; JPO;	
		repair)).ti,ab,clm.	DERWENT;	
			IBM_TDB	
-	3	((substrate and (insulating or insulator or	USPAT;	2003/01/27
		dielectric) and (gate) and (data) and pixel	US-PGPUB;	13:34
		and protrusion and (redundant or	EPO; JPO;	
		repair)).ti,ab,clm.) and (matrix or matrices)	DERWENT;	
			IBM_TDB	
-	2	(((substrate and (insulating or insulator or	USPAT;	2003/01/27
		dielectric) and (gate) and (data) and pixel	US-PGPUB;	13:33
		and protrusion and (redundant or	EPO; JPO;	
		repair)).ti,ab,clm.) and (matrix or matrices))	DERWENT;	
		and transparent	IBM_TDB	
	1797	((insulating or insulator or dielectric) and	USPAT;	2003/01/27
		(gate near line) and (data near line) and	US-PGPUB;	13:37
		pixel)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	54	(((insulating or insulator or dielectric) and	USPAT;	2003/01/27
		(gate near line) and (data near line) and	US-PGPUB;	13:41
		pixel)) and (matrix or matrices) and (color	EPO; JPO;	1
		ner filter) and transparent and protrusion	DERWENT;	
			IBM_TDB	

-	28	((((insulating or insulat r r dielectric) and	USPAT;	2003/01/27
		(gate n ar line) and (data near line) and	US-PGPUB;	13:48
1		pixel)) and (matrix or matrices) and (col r	EPO; JPO;	
		n r filt r) and transpar nt and protrusi n)	DERWENT;	
		and (organic) and (photoresist r	IBM_TDB	
		ph t -resist r ph t lithography or		
		photo-lithography or photosensitive or		
		photo-sensitive or resin or epoxy or mask or		
		masking or masked) and (etch or etching or		
		etched or etchant)		
-	25	(((((insulating or insulator or dielectric) and	USPAT;	2003/01/27
		(gate near line) and (data near line) and	US-PGPUB;	13:52
		pixel)) and (matrix or matrices) and (color	EPO; JPO;	
		ner filter) and transparent and protrusion)	DERWENT;	
		and (organic) and (photoresist or	IBM_TDB	
		photo-resist or photolithography or		
		photo-lithography or photosensitive or		
		photo-sensitive or resin or epoxy or mask or		
		masking or masked) and (etch or etching or		
		etched or etchant)) and (color near filter)		
-	3	((((((insulating or insulator or dielectric) and	USPAT;	2003/01/27
		(gate near line) and (data near line) and	US-PGPUB;	13:56
		pixel)) and (matrix or matrices) and (color	EPO; JPO;	
		ner filter) and transparent and protrusion)	DERWENT;	
		and (organic) and (photoresist or	IBM_TDB	
		photo-resist or photolithography or		• •
		photo-lithography or photosensitive or		
		photo-sensitive or resin or epoxy or mask or		
		masking or masked) and (etch or etching or		
		etched or etchant)) and (color near filter))		
		and image and (scan or scannig) and		
		(transmit or transmitting or transmitted or		
		transmission) and (switch or switching or		
		switched)		
-	16	((((((insulating or insulator or dielectric) and	USPAT;	2003/01/27
		(gate near line) and (data near line) and	US-PGPUB;	13:57
		pixel)) and (matrix or matrices) and (color	EPO; JPO;	
		ner filter) and transparent and protrusion)	DERWENT;	
		and (organic) and (photoresist or	IBM_TDB	
		photo-resist or photolithography or		
		photo-lithography or photosensitive or		
		photo-sensitive or resin or epoxy or mask or		
		masking or masked) and (etch or etching or		}
		etched or etchant)) and (color near filter))		
		and (black near (matrix or matrices))		

•	12	(((((((insulating or insulator or di lectric) and	USPAT;	2003/01/27
_		(gate near lin) and (data n ar line) and	US-PGPUB;	13:59
		pix I)) and (matrix r matric s) and (col r	EPO; JPO;	
		ner filter) and transparent and pr trusi n)	DERWENT;	
		and (rganic) and (photoresist r	IBM_TDB	
			10111_100	
		ph to-resist rph t lith graphy or		
		photo-lithography or photosensitive or		
		photo-sensitive or resin or epoxy or mask or		
		masking or masked) and (etch or etching or		!
		etched or etchant)) and (color near filter))		
		and (black near (matrix or matrices))) and		
		image	HEDAT.	2002/04/27
-	1	((((((((insulating or insulator or dielectric)	USPAT;	2003/01/27
		and (gate near line) and (data near line) and	US-PGPUB;	13:59
		pixel)) and (matrix or matrices) and (color	EPO; JPO;	
		ner filter) and transparent and protrusion)	DERWENT;	
		and (organic) and (photoresist or	IBM_TDB	
		photo-resist or photolithography or		
		photo-lithography or photosensitive or		
		photo-sensitive or resin or epoxy or mask or		
		masking or masked) and (etch or etching or		
		etched or etchant)) and (color near filter))		•
		and (black near (matrix or matrices))) and		
		image) and (redundant or repair)		
-	72	((redundant or repair) and gate and data and	USPAT;	2003/01/27
		pixel and (insulating or insulator or	US-PGPUB;	14:03
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		near crystal) or display)).ti,ab,clm.	DERWENT;	
			IBM_TDB	
-	33	(((redundant or repair) and gate and data	USPAT;	2003/01/27
		and pixel and (insulating or insulator or	US-PGPUB;	14:04
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gate near line)		
-	1	((((redundant or repair) and gate and data	USPAT;	2003/01/27
		and pixel and (insulating or insulator or	US-PGPUB;	14:05
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gate near line)) and (organic near black		
		near (matrix or matrices))		
_	1	((((redundant or repair) and gate and data	USPAT;	2003/01/27
_		and pixel and (insulating or insulator or	US-PGPUB;	14:10
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data near line) and	IBM_TDB	
1		(gate near line)) and (rganic sam (black	15.11_155	
		, , , , , , , , , , , , , , , , , , , ,		
	<u> </u>	near (matrix r matrices)))	<u> </u>	<u> </u>

•	5	((((r dundant or repair) and gate and data	USPAT;	2003/01/27
		and pixel and (insulating or insulator or	US-PGPUB;	14:14
		dielectric) and (lcd or liquid-crystal r (liquid	EPO; JPO;	
		near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data n ar lin) and	IBM_TDB	
		(gate near line)) and ((black near (matrix or		
		matrices)))		
-	2	(((((redundant or repair) and gate and data	USPAT;	2003/01/27
		and pixel and (insulating or insulator or	US-PGPUB;	14:20
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
	1 .	near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gate near line)) and ((black near (matrix or	<u>-</u>	
		matrices)))) and organic		
	20	((((redundant or repair) and gate and data	USPAT;	2003/01/27
•	20	and pixel and (insulating or insulator or	US-PGPUB:	14:28
			EPO; JPO;	17.20
		dielectric) and (lcd or liquid-crystal or (liquid	DERWENT;	
		near crystal) or display)).ti,ab,clm.) and	•	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gate near line)) and organic	LICDAT	2002/04/27
•	18	((((((redundant or repair) and gate and data	USPAT;	2003/01/27
		and pixel and (insulating or insulator or	US-PGPUB;	14:29
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gate near line)) and organic) and (pixel		
		same electrode) and (aperture or whole or		
		opening or gap or window)		
1	18	(((((redundant or repair) and gate and data	USPAT;	2003/01/27
		and pixel and (insulating or insulator or	US-PGPUB;	14:30
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		near crystal) or display)).ti,ab,clm.) and	DERWENT;	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gate near line)) and organic) and (pixel		
		near5 electrode) and (aperture or whole or		
		opening or gap or window)		
_	8	((((((redundant or repair) and gate and data	USPAT;	2003/01/27
•	9	and pixel and (insulating or insulator or	US-PGPUB;	14:31
		dielectric) and (lcd or liquid-crystal or (liquid	EPO; JPO;	
		1	DERWENT;	
		near crystal) or display)).ti,ab,clm.) and	1	
		(pixel and image) and (data near line) and	IBM_TDB	
		(gate near line)) and organic) and (pixel		
		near5 electrode) and (aperture or whole or		
		opening or gap or window)) and molecule		2222/21/27
•	5	(((((((redundant or repair) and gate and data	USPAT;	2003/01/27
		and pixel and (insulating or insulator or	US-PGPUB;	14:31
		dielectric) and (Icd or liquid-crystal or (liquid	EPO; JPO;	1
		n ar crystal) r display)).ti,ab,clm.) and	DERWENT;	
		(pix I and image) and (data n ar lin) and	IBM_TDB	
		(gat n ar lin)) and rganic) and (pix I		
		near5 ctr de) and (aperture r wh r		
		p ning rgap rwindow)) and m I cul)		
		and angle		

o ((((((() outline of Topall) and Sato and India	03/01/27 :32
and pix fand (modulating of modulation)	:32
dielectric) and (lcd or liquid-crystal or (liquid EPO; JPO;	
n ar crystal) r display)).ti,ab,clm.) and DERWENT;	
(pixel and image) and (data near line) and IBM_TDB	
(gat near lin)) and rganic) and (pixel	
near5 electrode) and (aperture or whole or	
opening or gap or window)) and molecule)	
and angle) and (scan or scanning or	
scanned)	
	03/01/27
	:41
dielectric) and (lcd or liquid-crystal or (liquid EPO; JPO;	
	ł
(gate near line)) and organic) and (pixel	
near5 electrode) and (aperture or whole or	
opening or gap or window)) and molecule)	ļ
and angle) and (scan or scanning or	
scanned)) and (transmission or transmit or	
transmitting or transmitted)	
((insulating of insulator of district of the state)	03/01/27
substrate same transparent same electrode US-PGPUB; 14	:45
same (light-blocking or (light near (block or EPO; JPO;	
blocking or blocked)) same metal same DERWENT;	
protrusion)) IBM_TDB	
- 1 (((insulating or insulator or dielectric) same USPAT; 20	03/01/27
substrate same transparent same electrode US-PGPUB; 14	l:46
same (light-blocking or (light near (block or EPO; JPO;	
blocking or blocked)) same metal same DERWENT;	
protrusion)).ti,ab,clm.) and organic IBM_TDB	
	03/01/27
	:46
same (light-blocking or (light near (block or EPO; JPO;	
blocking or blocked)) same metal same DERWENT;	
protrusion)).ti,ab,clm. IBM_TDB	
	03/01/27
	l:48
same (light-blocking or (light near (block or EPO; JPO;	
,	
protrusion)) and organic IBM_TDB	102/04/27
the state of the s	003/01/27
	1:49
same (light-blocking or (light near (block or EPO; JPO;	
blocking or blocked)) same metal same DERWENT;	
protrusion)) and organic) and (pixel near IBM_TDB	
electrode)	
. 4 (((insulating rinsulat rordi l ctric) sam USPAT; 20	003/01/27
substrat sam transpar nt same ! ctr d US-PGPUB; 15	5:05
sam (light-blocking r (light n ar (bl ck r EPO; JPO;	
blocking or bl ck d)) sam m tal sam DERWENT;	
pr trusi n)) and rganic) and (pix I) IBM_TDB	

•	3	(((insulating or insulat r or di l ctric) same	USPAT;	2003/01/27
		substrate same transparent sam ctrode	US-PGPUB;	14:50
		same (light-blocking r (light n ar (bl ck r	EPO; JPO;	
		bl cking r bl cked)) sam m tal sam	DERWENT;	
		pr trusion)) and organic) and	IBM_TDB	
		(pixel).ti,ab,clm.		
	3	((((insulating or insulator or dielectric) same	USPAT;	2003/01/27
		substrate same transparent same electrode	US-PGPUB;	14:53
		same (light-blocking or (light near (block or	EPO; JPO;	
		blocking or blocked)) same metal same	DERWENT;	
		protrusion)) and organic) and (pixel)) and	IBM_TDB	
		(thin near5 transistor)		